

High Efficient Rectifier Diode

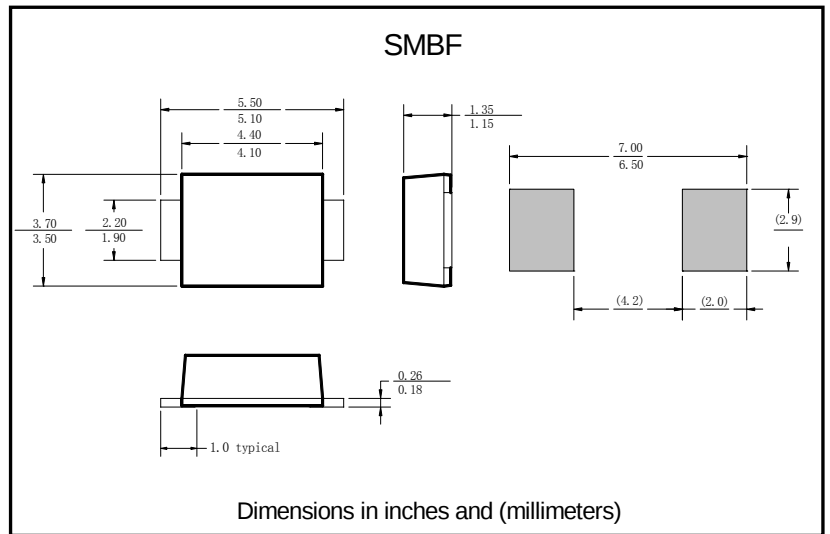
■特征 Features

- I_o 2.0A
- V_{RRM} 50V~1000V
- 玻璃钝化芯片
Glass passivated chip
- 耐正向浪涌电流能力高
High surge forward current capability

■用途 Applications

- 作一般电源单相整流
For general power supply
single-phase rectifier

■外形尺寸和印记 Outline Dimensions and Mark



■极限值（绝对最大额定值）

Limiting Values (Absolute Maximum Rating)

参数名称 Item	符号 Symbol	单位 Unit	条件 Conditions	US2						
				AF	BF	DF	GF	JF	KF	MF
反向重复峰值电压 Repetitive Peak Reverse Voltage	V_{RRM}	V		50	100	200	400	600	800	1000
平均整流输出电流 Average Rectified Output Current	I_o	A	60Hz单向半波, 电阻负载, $T_a=75^\circ\text{C}$ 60Hz One-way half-wave, R-load, $T_a=75^\circ\text{C}$	2.0						
正向（不重复）浪涌电流 Surge(Non-repetitive) Forward Current	I_{FSM}	A	60Hz正弦波, 一个周期, $T_j=25^\circ\text{C}$ 60Hz sine wave, 1 cycle, $T_j=25^\circ\text{C}$	50						
存储温度 Storage Temperature	T_{stg}	$^\circ\text{C}$		-55 ~ +150						
结温 Junction Temperature	T_j	$^\circ\text{C}$		-55 ~ +150						

■电特性（ $T_a=25^\circ\text{C}$ 除非另有规定）

Electrical Characteristics ($T_a=25^\circ\text{C}$ Unless otherwise specified)

参数名称 Item	符号 Symbol	单位 Unit	测试条件 Test Condition	US2						
				AF	BF	DF	GF	JF	KF	MF
正向峰值电压 Peak Forward Voltage	V _{FM}	V	I _{FM} =2.0A	1.0			1.3	1.7		
最大反向恢复时间 Maximum reverse recovery time	t _{rr}	ns	I _F =0.5A,I _R =1.0A,I _{RR} =0.25A	50				75		
反向峰值电流 Peak Reverse Current	I _{RRM}	μ A	V _{RM} =V _{RRM} , Ta=25℃	5						
热阻 Thermal Resistance	R θ J-L	℃/W	结和引线之间 Between junction and lead	20						

■特性曲线（典型） Characteristics(Typical)

Fig.1 Forward Current Derating Curve

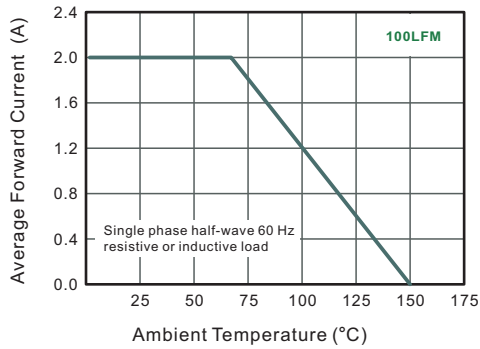


Fig.2 Typical Reverse Characteristics

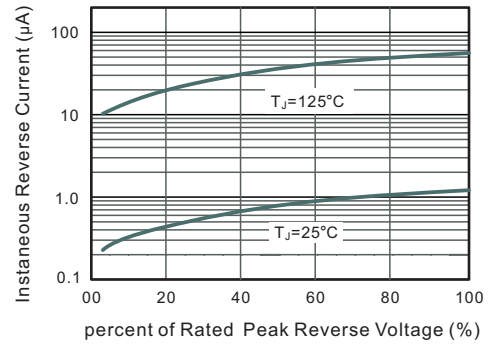


Fig.3 Typical Forward Characteristics

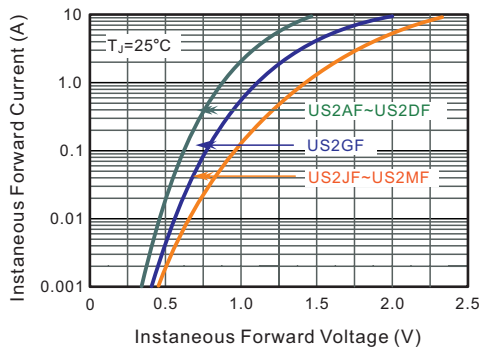


Fig.4 Maximum Non-Repetitive Peak Forward Surge Current

